

FIELD-EFFECT TRANSISTOR, DISPLAY ELEMENT, IMAGE
DISPLAY DEVICE, AND SYSTEM

ABSTRACT OF THE DISCLOSURE

5 A field-effect transistor including: a substrate; a passivation layer;
a gate insulating layer formed between the substrate and the passivation
layer; a source electrode and a drain electrode, which are formed to be in
contact with the gate insulating layer; a semiconductor layer, which is
formed at least between the source electrode and the drain electrode and
10 is in contact with the gate insulating layer, the source electrode, and the
drain electrode; and a gate electrode, which is in contact with the gate
insulating layer and faces the semiconductor layer via the gate insulating
layer, wherein the passivation layer contains a first complex oxide
containing an alkaline earth metal and a rare-earth element, and wherein
15 the gate insulating layer contains a second complex oxide containing an
alkaline earth metal and a rare-earth element.

[Fig. 1]